

General Description

The AO3401 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a load switch or in PWM applications. *Standard product AO3401 is Pb-free (meets ROHS & Sony 259 specifications). AO3401L is a Green Product ordering option. AO3401 and AO3401L are electrically identical.*

Features

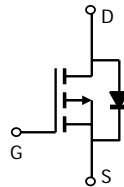
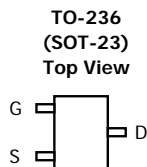
$$V_{DS} (V) = -30V$$

$$I_D = -4.2 A (V_{GS} = -10V)$$

$$R_{DS(ON)} < 50m\Omega (V_{GS} = -10V)$$

$$R_{DS(ON)} < 65m\Omega (V_{GS} = -4.5V)$$

$$R_{DS(ON)} < 120m\Omega (V_{GS} = -2.5V)$$



Absolute Maximum Ratings $T_A=25^\circ C$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ^A	$T_A=25^\circ C$	-4.2	A
	$T_A=70^\circ C$	-3.5	
Pulsed Drain Current ^B	I_{DM}	-30	
Power Dissipation ^A	$T_A=25^\circ C$	1.4	W
	$T_A=70^\circ C$	1	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ C$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	65	90	$^\circ C/W$
Maximum Junction-to-Ambient ^A		Steady-State	85	125
Maximum Junction-to-Lead ^C	$R_{\theta JL}$	43	60	$^\circ C/W$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D = -250μA, V _{GS} = 0V	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -24V, V _{GS} = 0V T _J = 55°C			-1 -5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} = 0V, V _{GS} = ±12V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-0.7	-1	-1.3	V
I _{D(ON)}	On state drain current	V _{GS} = -4.5V, V _{DS} = -5V	-25			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} = -10V, I _D = -4.2A T _J = 125°C		42	50	mΩ
		V _{GS} = -4.5V, I _D = -4A		53	65	
		V _{GS} = -2.5V, I _D = -1A		80	120	mΩ
g _{FS}	Forward Transconductance	V _{DS} = -5V, I _D = -5A	7	11		S
V _{SD}	Diode Forward Voltage	I _S = -1A, V _{GS} = 0V		-0.75	-1	V
I _S	Maximum Body-Diode Continuous Current				-2.2	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} = 0V, V _{DS} = -15V, f = 1MHz		954		pF
C _{oss}	Output Capacitance			115		pF
C _{rss}	Reverse Transfer Capacitance			77		pF
R _g	Gate resistance	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		6		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} = -4.5V, V _{DS} = -15V, I _D = -4A		9.4		nC
Q _{gs}	Gate Source Charge			2		nC
Q _{gd}	Gate Drain Charge			3		nC
t _{D(on)}	Turn-On Delay Time	V _{GS} = -10V, V _{DS} = -15V, R _L = 3.6Ω, R _{GEN} = 6Ω		6.3		ns
t _r	Turn-On Rise Time			3.2		ns
t _{D(off)}	Turn-Off Delay Time			38.2		ns
t _f	Turn-Off Fall Time			12		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F = -4A, dI/dt = 100A/μs		20.2		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F = -4A, dI/dt = 100A/μs		11.2		nC

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6, 12, 14 are obtained using 80μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

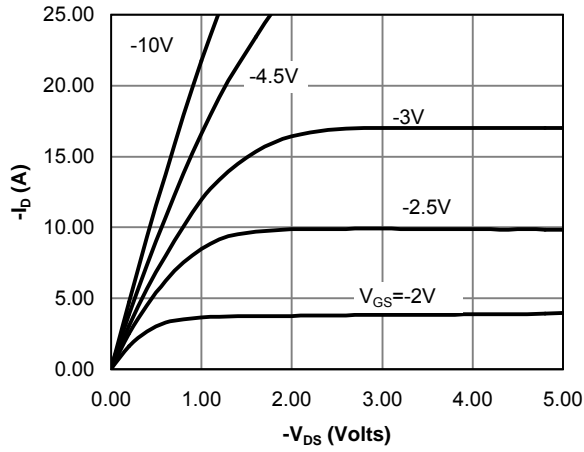


Fig 1: On-Region Characteristics

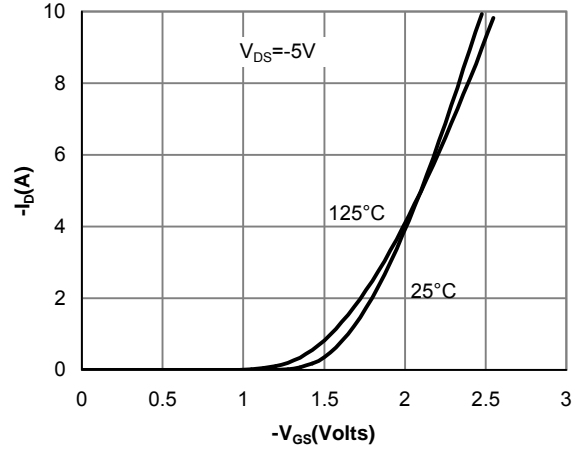


Figure 2: Transfer Characteristics

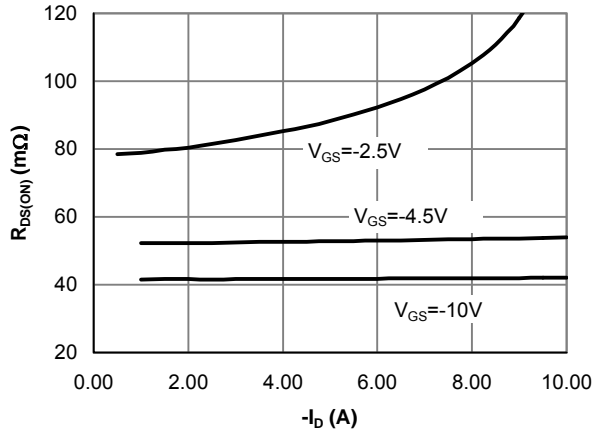


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

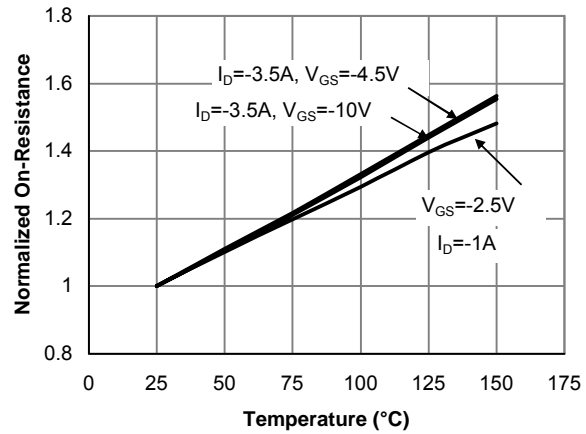


Figure 4: On-Resistance vs. Junction Temperature

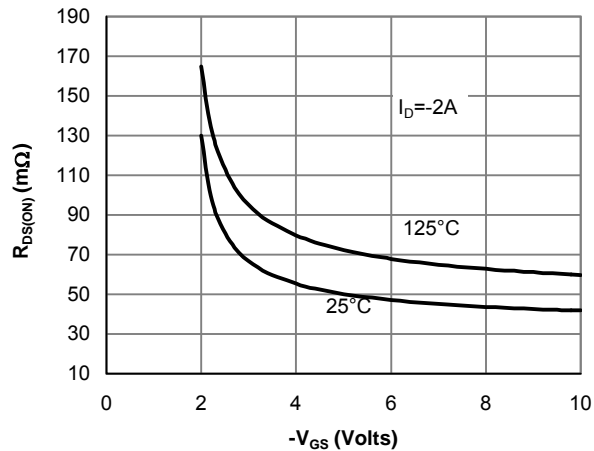


Figure 5: On-Resistance vs. Gate-Source Voltage

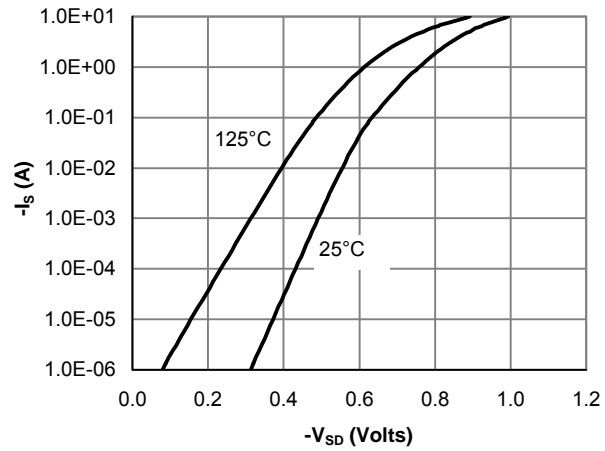


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

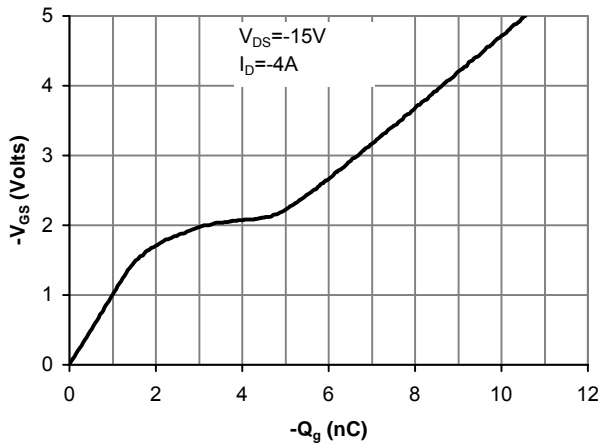


Figure 7: Gate-Charge Characteristics

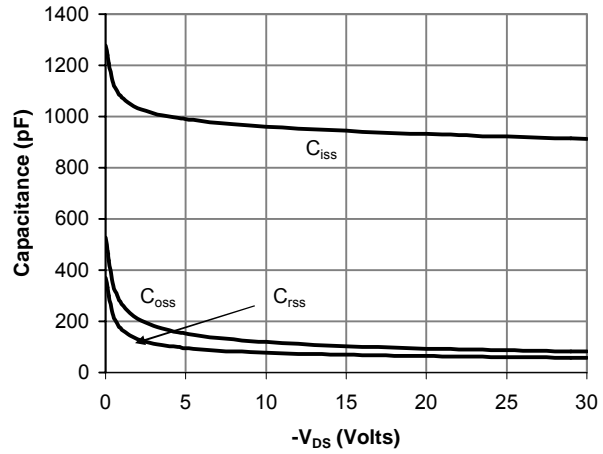


Figure 8: Capacitance Characteristics

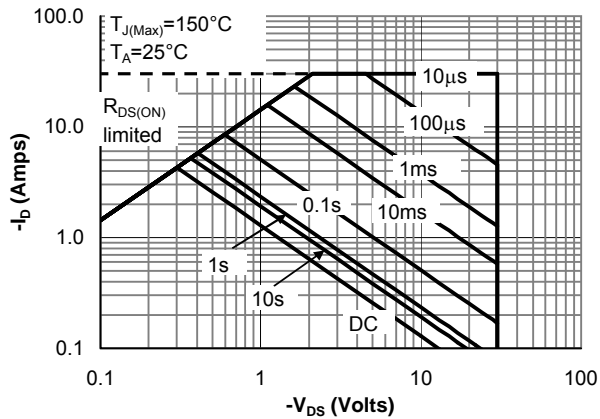


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

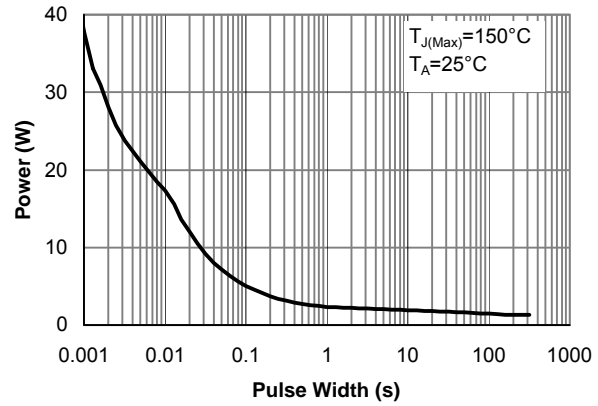


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

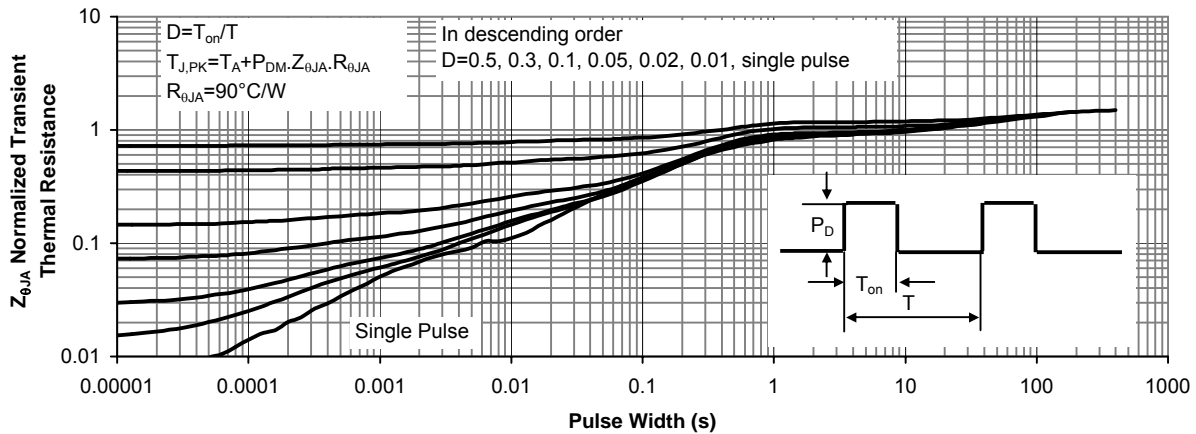


Figure 11: Normalized Maximum Transient Thermal Impedance